# TOSHIBA

TOSHIBA Photocoupler GaAlAs Ired & Photo IC

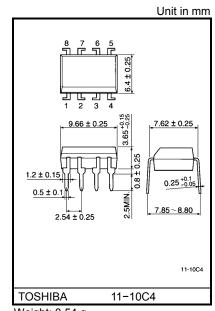
# TLP2630

Degital Logic Isolation Tele–Communication Analog Data Equipment Control Microprocessor System Interface

The TOSHIBA TLP2630 dual photocoupler consists of a pair of GaAlAs light emitting diode and integrated high gain, high speed photodetector.

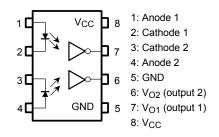
The output of the detector circuit is an open collector, schottky clamped transistor. This unit is 8–lead DIP.

- Input current threshold:  $I_F = 5mA(max.)$
- LSTTL/TTL compatible: 5V supply
- Switching speed: 10MBd(typ.)
- Guaranteed performance over temperature: 0~70°C
- Isolation voltage: 2500Vrms(min.)
- UL recognized:UL1577, file no. E67349





#### Pin Configuration (top view)

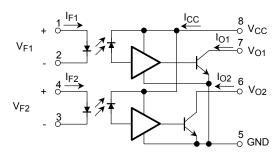


#### Truth Table (positive logic)

Input	Output
Н	L
L	Н

A 0.01 to 0.1 $\mu$ F bypass capacitor must connected between pins 8 and 5 (see Note 1).

#### Schematic



### Maximum Ratings (no derating required up to 70°C)

	Characteristic	Symbol	Rating	Unit
	Forward current(each channel)	l <sub>F</sub>	20	mA
LED	Pulse forward current (each channel)*	IFP	30	mA
	Reverse voltage(each channel)	V <sub>R</sub>	5	V
	Output current(each channel)	Ι <sub>Ο</sub>	16	mA
ъ	Output voltage(each channel)	Vo	-0.5~7	V
Detector	Supply voltage (1 minute maximum)	V <sub>CC</sub>	7	V
	Output collector power dissipation(each channel)	PO	40	mW
Oper	ating temperature range	T <sub>stg</sub> –55~125		°C
Stora	ge temperature range	T <sub>opr</sub>	opr -40~85	
Lead	soldering temperature (10 s) (Note 1)	T <sub>sol</sub>	260	°C
Isolat	ion voltage (AC, 1 min., R.H.≤ 60%, Note 3)	BVS	2500	Vrms

\* t  $\leq$  1 msec duration.

#### **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Input current, low level, each channel	I <sub>FL</sub>	0	_	250	μA
Input current, high level, each channel	IFH	6.3*	_	15	mA
Supply voltage, output	V <sub>CC</sub>	4.5	5	5.5	V
Fan out(TTL load, each channel)	N	_	_	8	
Operating temperature	T <sub>opr</sub>	0		70	°C

\* 6.3mA is a guard banded value which allows for at least 20% CTR degradation. Initial input current threshold value is 5.0mA or less.

## Electrical Characteristics (Ta = 0~70°C, unless otherwise noted)

Characteristic	Symbol	Test Condition		Min.	Тур.*	Max.	Unit
Input forward voltage (each channel)	VF	I <sub>F</sub> = 10mA, Ta = 25°C			1.65	1.75	V
Input diode temperature coefficient(each channel)	ΔV <sub>F</sub> / ΔTa	I <sub>F</sub> = 10mA			-2.0	_	mV / °C
Input reverse breakdown voltage(each channel)	BV <sub>R</sub>	I <sub>R</sub> = 10μΑ, Ta = 25°C		5	_	_	V
Input capacitance (each channel)	CT	V <sub>F</sub> = 0, f = 1MHz		_	45	_	pF
High level output current (each channel)	I <sub>OH</sub>	$V_{CC} = 5.5V, V_{O} = 5.5V$ $I_{F} = 250\mu A$		_	1	250	μA
Low level output voltage (each channel)	V <sub>OL</sub>	$V_{CC}$ = 5.5V, I <sub>F</sub> = 5mA I <sub>OL</sub> (sinking) = 13mA		_	0.4	0.6	V
High level supply current (both channels)	Іссн	V <sub>CC</sub> = 5.5V, I <sub>F</sub> = 0		_	14	30	mA
Low level supply current (both channels)	ICCL	V <sub>CC</sub> = 5.5V, I <sub>F</sub> = 10mA		_	24	36	mA
Isolation voltage	R <sub>S</sub>	V <sub>S</sub> = 500V, R.H.≤ 60%	(Note 3)	_	10 <sup>14</sup>	_	Ω
Capacitance(input-output)	CS	f = 1MHz	(Note 3)	_	0.6		pF
Input–input leakage current	I <sub>I-I</sub>	R.H.≤ 60%, t = 5s V <sub>I−I</sub> = 500V	(Note 6)		0.005	_	μA
Resistance(input-input)	R <sub>I-I</sub>	V <sub>I-I</sub> = 500V	(Note 6)		10 <sup>11</sup>		Ω
Capacitance(input-input)	C <sub>I-I</sub>	f = 1MHz	(Note 6)		0.25		pF

\* All typical values are at V<sub>CC</sub> = 5V, Ta =  $25^{\circ}$ C.

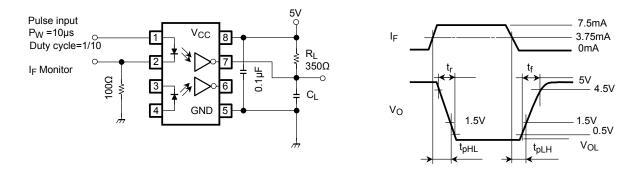
#### Switching Characteristics (Ta =25°C , V<sub>CC</sub>=5V)

Characteristic	Symbol	Test Cir– cuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay time to low output level	t <sub>pHL</sub>	1	$I_F = 0 \rightarrow 7.5 \text{mA}, R_L = 350\Omega$ $C_L = 15 \text{pF}$ (each channel)	_	60	75	ns
Propagation delay time to high output level	t <sub>pLH</sub>	1	$I_F = 7.5 \text{mA} \rightarrow 0$ , $R_L = 350 \Omega$ $C_L = 15 \text{pF}$ (each channel)		60	75	ns
Output rise a time,output fall time(10~90%)	t <sub>r</sub> ,t <sub>f</sub>	1	$I_F = 0 \overrightarrow{\leftarrow} 7.5 \text{mA}, R_L = 350 \Omega$ $C_L = 15 \text{pF}$ (each channel)		30		ns
Common mode transient immunity at high output level	CM <sub>H</sub>	2	$\begin{array}{l} I_{F} = 0, \ R_{L} = 350\Omega \\ V_{CM} = 200V \\ V_{O}(min.) = 2V \\ (each channel, Note 4) \end{array}$	_	200	_	V / µs
Common mode transient immunity at low output level	CML	2	$\begin{array}{l} I_F = 7.5 \text{mA},  R_L = 350 \Omega \\ V_{CM} = 200 V \\ V_O(\text{max.}) = 0.8 V \\ (\text{each channel, Note 5}) \end{array}$		-500		V / µs

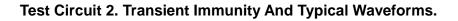
(Note 1) 2mm below seating plane.

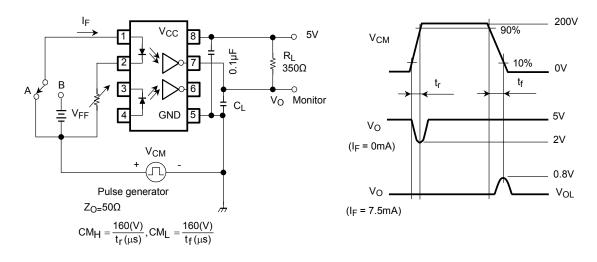
- (Note 2) The V<sub>CC</sub> supply voltage to each TLP2630 isolator must be bypassed by a  $0.01\mu$ F capacitor or larger. This can be either a ceramic or solid tantalum capacitor with good high frequency characteristic and should be connected as close as possible to the package V<sub>CC</sub> and GND pins each device.
- (Note 3) Device considered a two-terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.
- (Note 4) CM<sub>H</sub> · the maximum tolerable rate of rise of the common mode voltage to ensure the output will remain in the high state(i.e.,  $V_{OUT} > 2.0V$ )
- (Note 5) CM<sub>L</sub> · the maximum tolerable rate of fall of the common mode voltage to ensure the output will remain in the low output state(i.e.,  $V_{OUT} > 0.8V$ )
  - Measured in volts per microsecond(V /  $\mu$ s).
- (Note 6) Measured between pins 1 and 2 shorted together, and pins 3 and 4 shorted together.

## Test Circuit 1. tpHL And tpLH



\* C<sub>L</sub> is approximately 15pF which includes probe and stray wirng capacitance.





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30

50

5 10

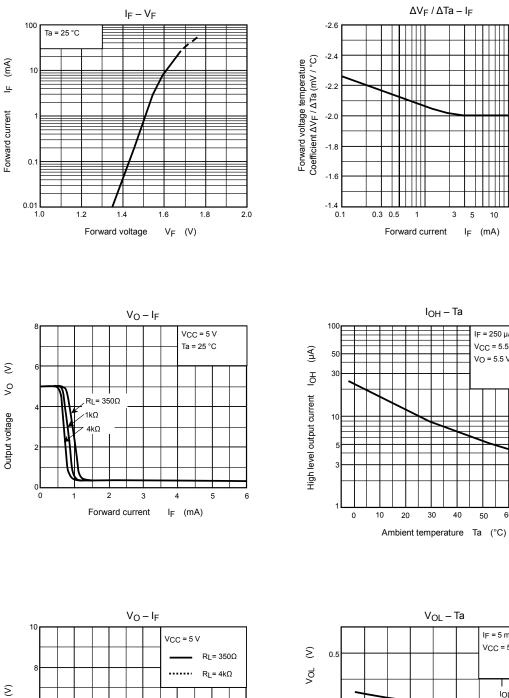
I<sub>F</sub> (mA)

IF = 250 μA V<sub>CC</sub> = 5.5 V

VO = 5.5 V

60 50

70



ו | |

6

6

5

V<sub>OL</sub> – Ta IF = 5 mA VCC = 5.5 V IOL=16mA Low level output voltage 0.4 12.8mA 9.6mA 6.4mA 0.3 0.2

0

20

40

Ambient temperature Ta (°C)

60

Downloaded from Elcodis.com electronic components distributor

Ta= 70°C 0°C

2

Forward current

3

4

I<sub>F</sub> (mA)

Ļ

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1

2

0

0

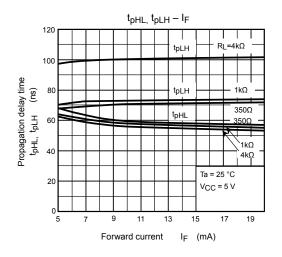
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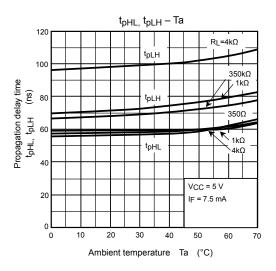
Output voltage

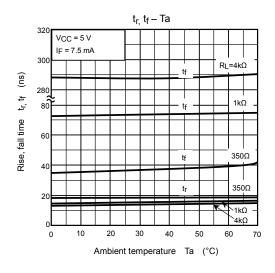
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